Form PTO-1449 (modified)	Atty. Docket No.: 11762.0284.CNUS01	Serial No.: 09/923,058
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U.S. Patent Documents

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GPG	A45	5,364,804	11/15/1994	Ho, et al.	437	41	11/03/93
	A46	5,376,233	12/27/1994	Man	156	662	12/30/92
	A47	5,423,945	06/13/1995	Marks, et al.	156	662.1	09/08/92
	A48	5,429,710	07/04/1995	Akiba, et al.	216	17	02/16/94
	A49	5,451,290	09/19/1995	Salfelder	216	67	02/11/93
	A50	5,468,342	11/21/1995	Nulty, et al.	156	643.1	04/28/94
	A51	5,470,768	11/28/1995	Yanai, et al.	437	40	08/05/93
	A52	5,477,975	12/26/1995	Rice, et al.	216	68	10/15/93
	A53	5,503,901	04/02/1996	Sakai, et al.	428	161	06/29/94
	A54	5,556,501	09/17/1996	Collins, et al.	156	345	04/01/93
	A55	5,562,801	10/08/1996	Nulty, J.E.	156	643.1	12/07/94
	A56	5,772,832	06/30/1998	Collins, et al.	156	345	04/04/97
	A57	5,880,036	03/09/1999	Becker, et al.	438	740	11/15/93
	A58	5,880,037	03/09/1999	Arleo, P.	438	740	10/09/97
	A59	5,888,414	03/30/1999	Collins, et al.	216	68	09/24/97
	A60	6,184,150	02/06/2001	Yang, et al.	438	740	10/27/97
GPG	A61	6,194,325	02/27/2001	Yang, et al.	438	740	12/04/95

Foreign Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Country	~~Class~~	~~Sub Class~~	~~Translation Yes/No~~
GPG	B1	55009464	01/23/1980	Japan	~~H01L~~	27/08	~~Abstract Only~~
GPG	B2	0 050 972 A2	05/05/1982	EPO	~~H01L~~	~~21/88~~	~~Yes~~

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GMG	B3	57210631	12/24/1982	Japan	[illegible]	[illegible]	[illegible]
	B4	60111474	06/17/1985	Japan	[illegible]	[illegible]	[illegible]
	B5	61-224423	10/06/1986	Japan	[illegible]	[illegible]	[illegible]
	B6	0 265 584 A2	05/04/1988	EPO	[illegible]	[illegible]	[illegible]
	B7	2 175 542 A	12/03/1986	United Kingdom	[illegible]	[illegible]	[illegible]
	B8	01-15930	01/19/1989	Japan	[illegible]	[illegible]	[illegible]
	B9	2062038	03/01/1990	Japan	[illegible]	[illegible]	[illegible]
	B10	4-180222	06/26/1992	Japan	[illegible]	[illegible]	[illegible]
	B11	4-298032	10/21/1992	Japan	[illegible]	[illegible]	[illegible]
	B12	0 520 519 A1	12/30/1992	EPO	[illegible]	[illegible]	[illegible]
	B13	0 552 490 A1	07/28/1993	EPO	[illegible]	[illegible]	[illegible]
	B14	0 644 584 A1	03/22/1995	EPO	[illegible]	[illegible]	[illegible]
	B15	0 651 434 A2	05/03/1995	EPO	[illegible]	[illegible]	[illegible]
GMG	B16	58-53833	03/30/1983	Japan	[illegible]	[illegible]	[illegible]

Other Art (Including Author, Title, Date Pertinent Pages, Etc.)

Exam. Init.	Ref. Des.	Citation
GMG	C1	Watanabe, S., "Plasma Cleaning by Use of Hollow-Cathode Discharge in a CHF_3-SiO_2 Dry-Etching System", *Japanese J. Appl. Physics* **1992**, 31; 1491-1498.
	C2	Yasuaki Nagahiro, "Self-Aligned Contact Development Activity Increases Aimed for Large Scale Manufacturing Around 0.25 Mm Era Problem of Etching Technology: Improvement of Si_3N_4 Selectivity Ratio", *Nikkei Microdevices*, Feb. **1995**, pp. 54-61.
GMG	C3	Gottscho, R.A., "Recent Developments in Plasma Processing", AT&T Bell Laboratories, 1994, *American Vacuum Society Symposium*, p. 120.

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Exam. Init.	Ref. Des.	Citation
	C4	Nulty, J.E.; Trammel, P.S., "Self-Aligned Contact (SAC) Dry Etch Process of 0.5m SRAM Technology", *1994 American Vacuum Society Symposium*, p. 120.
	C5	"The Correlation Between Selective Oxide Etching and Thermodynamic Prediction", S.C. McNevin, AT&T Bell Laboratories, *1994 American Vacuum Society Symposium*, p. 120.
	C6	Horiike, Y.; Kubota K.; Fukazawa T., "High Rate and Highly Selective SiO_2 Etching Employing Inductively Coupled Plasma", Tokyo University, *1994 American Vacuum Society Symposium*, p. 120.
	C7	Yin, G.Z.; Ben-Dor, M.; Chang, M.S.; Yep, T.O. "High-Selectivity Plasma Etching of Silicon Dioxide on Single-Wafer Etchers", *Journal of Vacuum Science & Technology A* **1989**, A7(3); 691-695.
	C8	Bariya, A.J.; Shan, H.; Frank, C.W.; Self, S.A.; McVittie, J.P., "The Etching of CHF_3 Plasma Polymer in Fluorine-Containing Discharges", *Journal of Vacuum Science and Technology B* **1991**, 9 (1); 1-7.
	C9	Machida, K.; Oikawa, H., "SiO_2 Planarization Technology with Biasing and Electron Cyclotron Resonance Plasma Deposition for Submicron Interconnections", *Journal of Vacuum Science and Technology B* **1986**, 4; 818-821.
	C10	Anonymous, "Selective Reactive Ion Etch for Silicon Oxide Over Silicon Nitride", *Research Disclosure* **1989**, 301; 340.
	C11	Moss, S.J., et al. Eds. "Plasma Etching", in *The Chemistry of the Semiconductor Industry*, New York: Blackie & Son Ltd., 1987, pp. 374-378.
	C12	D'Agostino, R., "Summary Abstract: Mechanisms of Polymerization in Discharges of Fluorocarbons", *Journal of Vacuum Science and Technology A* **1985**, 3 (6); 2627-2628.
	C13	Riley, P.E.; Hanson, D.A., "Comparison of Etch Rates of Silicon Nitride, Silicon Dioxide, and Polycrystalline Silicon Upon O_2 Dilution of CF_4 Plasmas", *Journal of Vacuum Science and Technology B* **1989**, 7(6); 1352-1356.
	C14	Gottlieb, S.; Oehrlein, G.S.; Lee, Y.H., "Reactive Ion Etching Related Si Surface Residues and Subsurface Damage: Their Relationship to Fundamental Etching Mechanisms", *Journal of Vacuum Science and Technology A* **1987**, 5 (4); 1585-1594.

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Exam. Init.	Ref. Des.	Citation
gpg	C15	Gilboa, H.; Hata, W.; O'Donnell, K., "Nondestructive Characterization of RIE Induced Radiation Damage Using Surface Accoustic Waves", *Mat. Res. Soc. Symp. Proc.* **1985**, 38 511-517.
	C16	Truesdale, B.A.; Smolinsky, G.; Mayer, T.M., "The Effect of Added Acetylene on the RF Discharge Chemistry of C_2F_6, A Mechanistic Model for Fluorocarbon Plasmas", *J. Applied Physics* **1980**, 51(5); 2909-2913.
	C17	Norström, H.; Buchta, R.; Runovc, F.; Wiklund, P., "RIE of SiO_2 in Doped and Undoped Fluorocarbon Plasmas", *Vacuum* **1982**, 32 (12); 737-745.
	C18	Coburn, J.W., "Increasing the Etch Ratio ofSiO_2/Si in Fluorocarbon Plasma Etching", *IBM Technical Disclosure, Bulletin* **1977**, 19 (10); 3854.
	C19	Arends, H.T.; DeVries, C.A.M.; van Roosmalen, A.J.; Puylaert, G.C.C., "Mass Spectrometry and Reactive Ion Etching of Silicon Nitride (Si_3N_4), Silicon Dioxide, and Silicon in Freon on Various Electrode Materials", in *Symposium Proceedings—International Symposium of Plasma Chemistry*, Vol. 3, 7th Ed.; Eindrove Publishers: 1985; 1007-1012.
	C20	Clarke, P.E.; Field, D.; Hydes, A.J.; Klemper, D.F.; Seakins, M.J., "Mass Spectrometric Studies of Plasma Etching of Silicon Nitride", *Journal of Vacuum Science and Technology, B*, Vol. 3, No. 6 (November, 1985), pp. 1614-1619.
	C21	Dalton, T.J.; Arnold, J.C.; Sawin, H.H.; Swan, S.; Corliss, D., "Microtrench Formation in Polysilicon Plasma Etching Over Thin Gate Oxide", *Journal of the Electrochemical Society*, Vol. 140, no. 8 (August, 1993), pp. 2395-2401.
	C22	Hikosaka, Y.; Sugai, H., "Radical Kinetics in a Flurocarbon Etching Plasma", *Japanese Applied Physics*, Vol. 32, no. 6 (June, 1993), pp. 3040-3044.
	C23	Li, Y.X.; Laros, M.; Sarro, P.M.; French, P.J.; Wolffenbuttel, R.F., "Plasma Etching of Polysilicon/Nitride/Polysilicon Sandwich Structure for Sensor Applications", *Microelectronic Engineering*, Vol. 21 (1993), pp. 341-344.
gpg	C24	Lindstrom, J.L.; Oehrlein, G.S.; Lanford, W.A., "RIE of Silicon Nitride Deposited by Different Methods in CF_4/H_2 Plasmas", *Journal of the Electrochemical Society*, Vol. 139, No. 1 (January, 1992), pp. 317-320.

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Exam. Init.	Ref. Des.	Citation
	C25	Samukawa, S., "Time-Modulated ECR Plasma Discharge for Controlling Polymerization in SiO_2 Etching", *Jpn. Journal of Applied Physics*, Vol. 32, part 1, no. 12B (December, 1993), pp. 6080-6087.
	C26	Sato, M.; Takehara, D.; Uda, K.; Sakiyama, K.; Hara, T., "Suppression of Microloading Effect by Low-Temperature SiO_2 Etching", *Jpn. Journal of Applied Physics*, Vol. 31, no. 12B (December, 1992), pp. 4370-4375.
	C27	Misaka, A.; Harafuji, K.; Kubota, M.; Nomura, N., "Novel Surface Reaction Model in Dry-Etching Process Stimulator", *Jpn. Journal of Applied Physics*, Vol. 31, Pt. 1, No. 12B (December, 1992), pp. 4363-4369.
	C28	Gottlieb, S.; Oehrlein, G.S.; Williams, H.L., "Silicon Etching Mechanisms in a CF_4/H_2 Glow Discharge", *Journal of Applied Physics*, Vol. 62, no. 2 (July, 1987), pp. 662-672.
	C29	Ohiwa, T.; Horioka, K.; Arikado, T.; Hasegawa, I.; Okano, H., "SiO_2 Tapered Etching Employing Magnetron Discharge of Fluorocarbon Gas", *Jpn. Journal of Applied Physics.*, Vol. 31, Pt. 1, no. 2A (1992), pp. 405-410.
	C30	Bondur, et al., "Gas Mixing to Prevent Polymer Formation During Reactive Ion Etching", *IBM Technical Disclosure Bulletin*, Vol. 21, no. 10 (March, 1979), p. 4016.
	C31	Kaga, T., et al., "Crown-Shaped Capacitor Cell for 1.5 V Operation 65 Mb DRAM's", *IEEE Transactions on Electronic Devices*, Vol. 38, no. 2 (1991), pp. 225-261.
	C32	Kure, T., et al., "VLSI Device Fabrication Using Unique, Highly-Selective Si_3N_4 Dry Etching", Proceedings of the International Electron Devices Meeting (IEDM), 1983, pp. 757-759.
	C33	Riley, P.E.; Young, K.K.; Liu, C.C., "Formation of Contacts in a Planarized $SiO_2/Si_3N_4/SiO_2$ Dielectric Structure", Journal of the Electrochemical Society, Vol. 139, no. 9 (September, 1992), pp. 2613-2616.
	C34	Becker, D.S.; Blalock, G., "A Method of Obtaining a High Oxide to Nitride Selectivity in an MERIE Reactor", 1993 Symposium of the Dielectric Science and Technology and Electronics Divisions of the Electrochemical Society, Vol. 93-21 (May 19, 1993), pp. 178-189.
	C35	Armacost, M.; Marks, J.; C.I. Yang, "Selective Oxide: Nitride Dry Etching in a High Density Plasma Reactor", Symposium of Dielectric Science and Technology and Electronics Divisions of the Electrochemical Society, Vol. 93-21, (May 19, 1993), pp. 190-200.

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Exam. Init.	Ref. Des.	Citation
	C36	Kuesters, K.H.; Muekhoff, H.M.; Enders, G.; Mohr, E.G.; Mueller, W., "Self-Aligned Bitline Contact for 4-Mbit DRAM", Extended Abstracts, The Electrochemical Society, Vol. 87-1 (1987), pp. 640-649.
	C37	Kenney, et al., "A Buried-Plate Trench Cell for a 64-Mb DRAM", 1992 Symposium of VLSI, *IEEE*.
	C38	Kusters, K.H.; Enders, G.; Meyberg, W.; Benzinger, H.; Hasler, B.; Higelin, G.; Rohl, S.; Muhlhoff, H.M.; Muller, W., "A High Density 4 Mbit DRAM Process Using a Fully Overlapping Bitline Contact (FoBIC) Trench Cell", *1987 Symposium on VLSI Technology Digest of Technical Papers*, pp. 93-94.
	C39	Nawata, M.; Kakehi, Y.; Kanai, S.; Kawasaki, Y.; Tsunokuni, K.; Enami, H., "High-Rate and Highly Selective Etching of SiO_2 Using Microwave Plasma", *183rd Meeting Electrochemical Society*, Honolulu, Hawaii 1993, pp. 228-234.
	C40	Arnold, J.C.; Gray, D.C.; Swain, H.H., "Influence of Reactant Transport on Fluorine RIE of Deep Trenches in Si", *Journal of Vacuum Science and Technology, B.*, Vol. 11, no. 6 (November, 1993), pp. 2071-2080.
	C41	Barklund, A.M.; Blom, H.O., "Influence of Different Etching Mechanisms on the Angular Dependence of Silicon Nitride Etching", *Journal of Vacuum Science and Technology, A.*, Vol. 11, no. 4 (July 1993), pp. 1226-1229.
	C42	Loewenstein, "Temperature Dependence of Silicon Nitride Etching by Atomic Fluorine", *Journal of Applied Physics*, Vol. 65, no. 1 (1989), pp. 386-387.
	C43	Loewenstein, "Selective Etching of Silicon Nitride Using Remote Plasmas of CF_4 and SF_6," *Journal Vac. Sci. Technology*, Vol. 7, no. 3 (1989), pp. 686-690.
	C44	Bondur, J.A.; Crimi, C.F., "Gas Mixing to Prevent Polymer Formation During Reactive Icon Etching", *IBM Technical Disclosure Bulletin*, Vol. 21, no. 10 (March, 1979).
	C45	Complaint for Declaratory Relief, filed in *Sandisk Corp. v. Micron Tech., Inc.*, Case No. C-02-2627VRW (N. D. Cal.).

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GMG	A1	3,479,237	11/18/1969	Bergh, et al.	156	11	04/08/66
	A2	4,180,432	12/25/1979	Clark	156	643	12/19/77
	A3	4,241,165	12/23/1980	Hughes, et al.	430	269	09/05/78
	A4	4,244,752	01/13/1981	Henderson, et al.	148	1.5	03/06/79
	A5	4,324,611	04/13/1982	Vogel, et al.	156	643	06/26/80
	A6	4,350,578	09/21/1982	Frieser, et al.	204	192 R	05/11/81
	A7	4,368,092	01/11/1983	Steinberg, et al.	156	345	08/05/81
	A8	4,374,698	02/22/1983	Sanders, et al.	156	643	07/09/81
	A9	4,377,438	03/22/1983	Moriya, et al.	156	643	09/22/81
	A10	4,401,054	08/30/1983	Matsuo, et al.	118	723	04/27/81
	A11	4,439,270	03/27/1984	Powell, et al.	156	644	08/08/83
	A12	4,492,620	01/08/1985	Matsuo, et al.	204	192 R	09/09/83
	A13	4,511,430	04/16/1985	Chen, et al.	156	643	01/30/84
	A14	4,568,410	02/04/1986	Thornquist	156	643	12/20/84
	A15	4,581,101	04/08/1986	Senoue, et al.	156	643	10/04/84
	A16	4,675,073	06/23/1987	Douglas, M.	156	643	03/07/86
	A17	4,711,698	12/08/1987	Douglas, M.	156	643	07/15/85
	A18	4,734,152	03/29/1988	Geis, et al.	156	646	07/13/87
	A19	4,734,157	03/29/1988	Carbaugh, et al.	156	643	03/18/87
	A20	4,778,561	10/18/1988	Ghanbari, E.	156	643	10/30/87
	A21	4,789,560	12/06/1988	Yen	427	96	01/08/86
GMG	A22	4,807,016	02/21/1989	Douglas, M.	357	67	11/20/87

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GM	A23	4,870,245	09/26/1989	Price, et al.	219	121.36	04/01/85
	A24	4,877,641	10/31/1989	Dory	427	38	05/31/88
	A25	4,892,753	01/09/1990	Wang, et al.	427	38	10/26/88
	A26	4,912,061	03/27/1990	Nasr	437	44	04/04/88
	A27	4,918,031	04/17/1990	Flamm, et al.	437	225	12/28/88
	A28	4,948,458	08/14/1990	Ogle, J.S.	156	643	08/14/89
	A29	4,971,655	11/20/1990	Stefano, et al.	156	659.1	12/26/89
	A30	4,978,420	12/18/1990	Bach	156	643	01/03/90
	A31	5,013,398	05/07/1991	Long, et al.	156	643	05/29/90
	A32	5,013,692	05/07/1991	Ide, et al.	437	241	12/05/89
	A33	5,021,121	06/04/1991	Groechel, et al.	156	643	02/16/90
	A34	5,040,046	08/13/1991	Chhabra, et al.	357	54	10/09/90
	A35	5,043,790	08/27/1991	Butler	357	68	04/05/90
	A36	5,091,326	02/25/1992	Haskell, J.D.	437	43	09/12/90
	A37	5,093,277	03/03/1992	Arima, et al.	437	69	03/02/90
	A38	5,242,538	09/07/1993	Hamrah, et al.	156	643	01/29/92
	A39	5,269,879	12/14/1993	Rhoades, et al.	156	643	10/16/91
	A40	5,286,344	02/15/1994	Blalock, et al.	156	657	06/15/92
	A41	5,286,667	02/15/1994	Lin, et al.	437	52	08/11/92
	A42	5,296,095	03/22/1994	Nabeshima, et al.	156	662	10/30/91
	A43	5,316,616	05/31/1994	Nakamura, et al.	156	643	05/27/93
GM	A44	5,338,398	08/16/1994	Szwejkowski, et al.	156	655	12/23/92

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